



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	30V
I_D	5.6A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	25mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	31mohm
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	45mohm
V_{DS} Tested	

General Description

Trench Power LV MOSFET technology
High density cell design for low $R_{DS(ON)}$
High Speed switching

Applications

Battery protection
Load switch
Power management

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	± 12	V
Drain Current	$T_A=25^\circ\text{C}$	I_D	5.6	A
	$T_A=70^\circ\text{C}$		4.5	
Pulsed Drain Current ^A		I_{DM}	23	A



Electrical Characteristics (T_j=25 unless otherwise noted)

Parameter	Symbol
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Typical Performance Characteristics

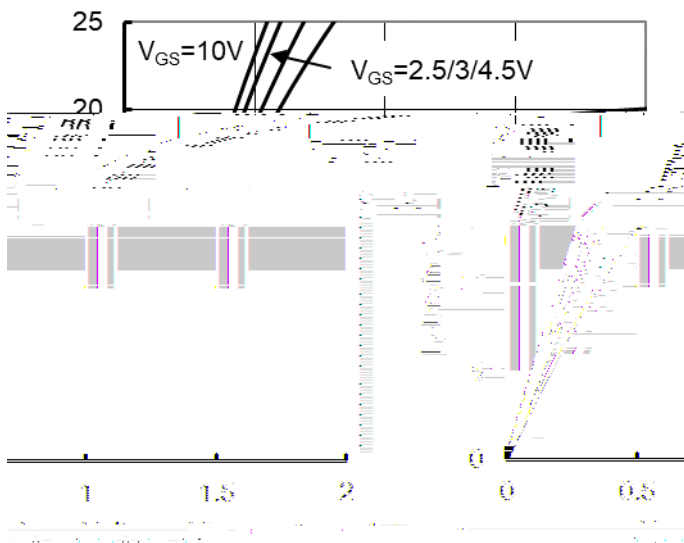


Figure1. Output Characteristics

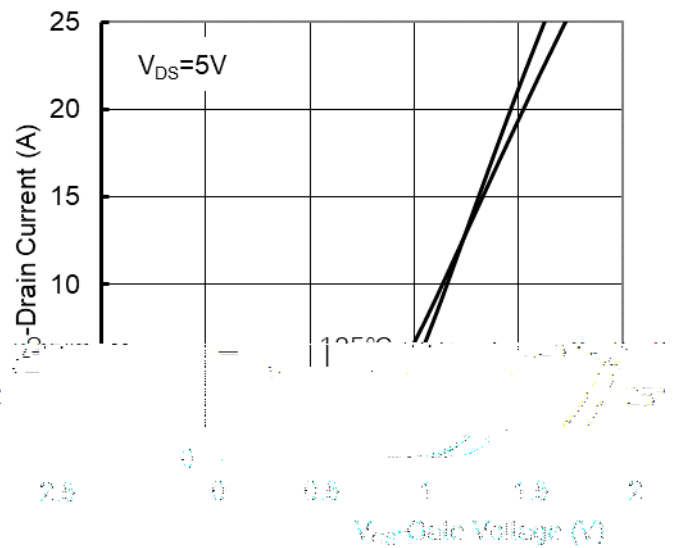


Figure2. Transfer Characteristics

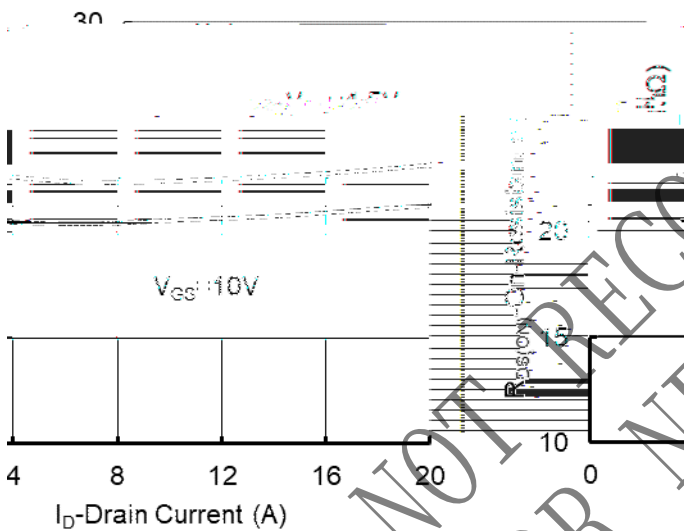


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

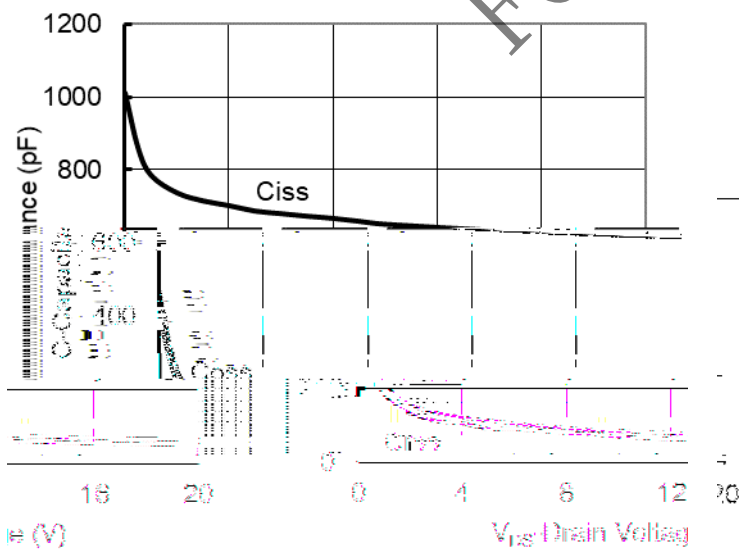


Figure5. Capacitance Characteristics

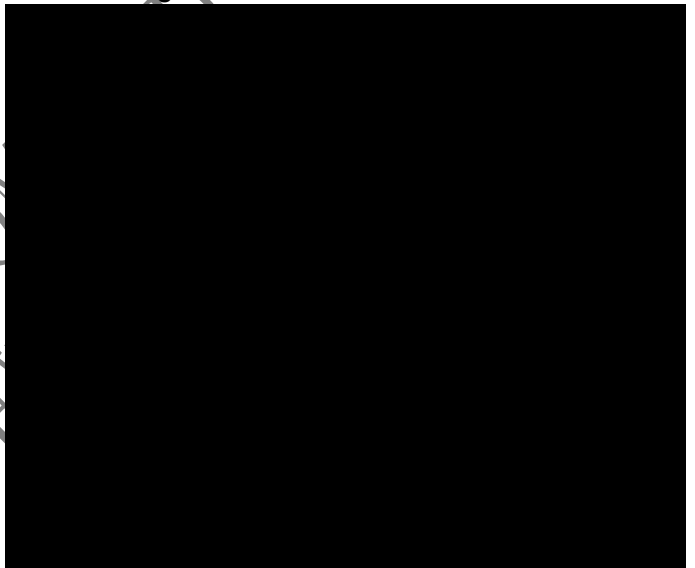


Figure 4: On-Resistance vs. Junction Temperature

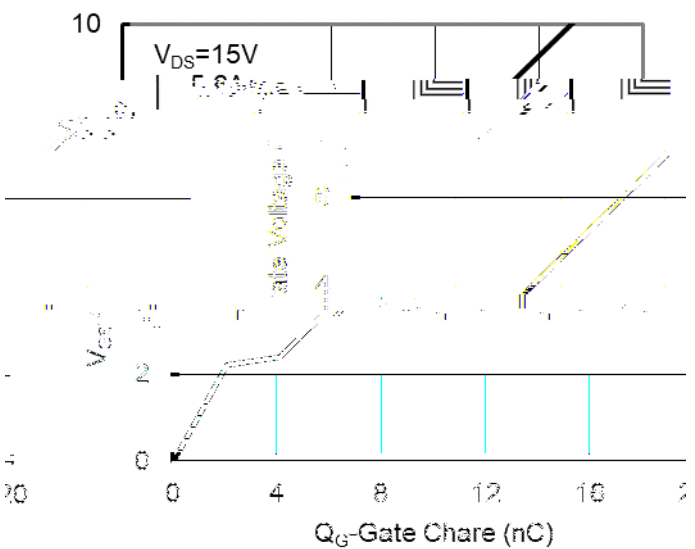


Figure6. Gate Charge

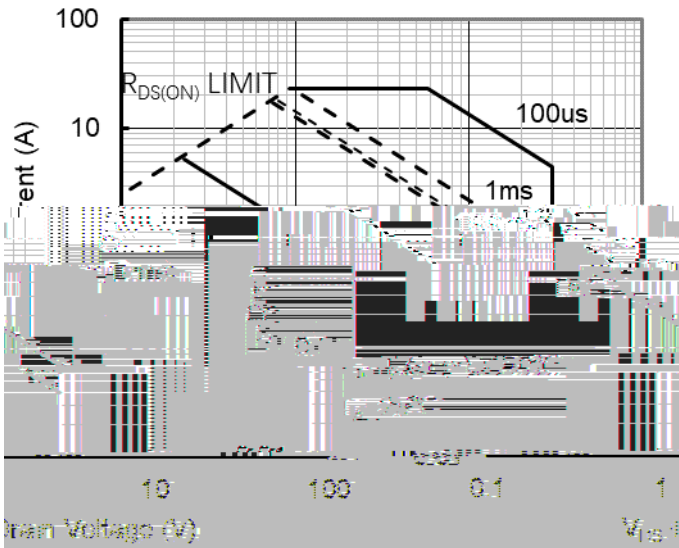


Figure7. Safe Operation Area

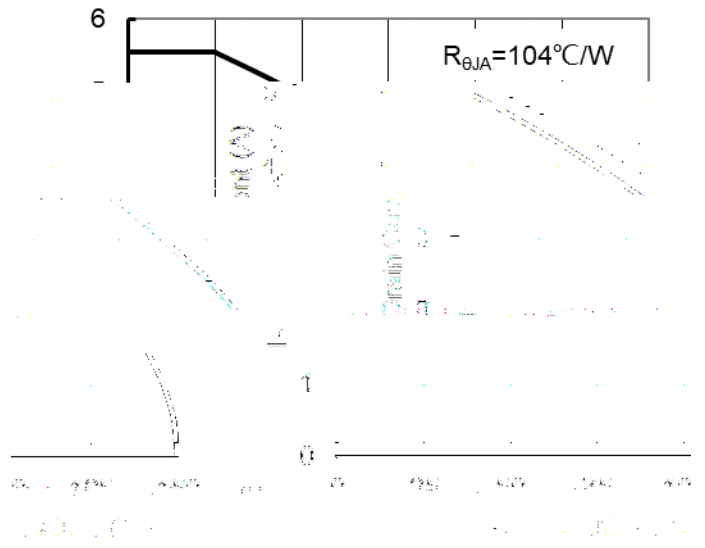


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

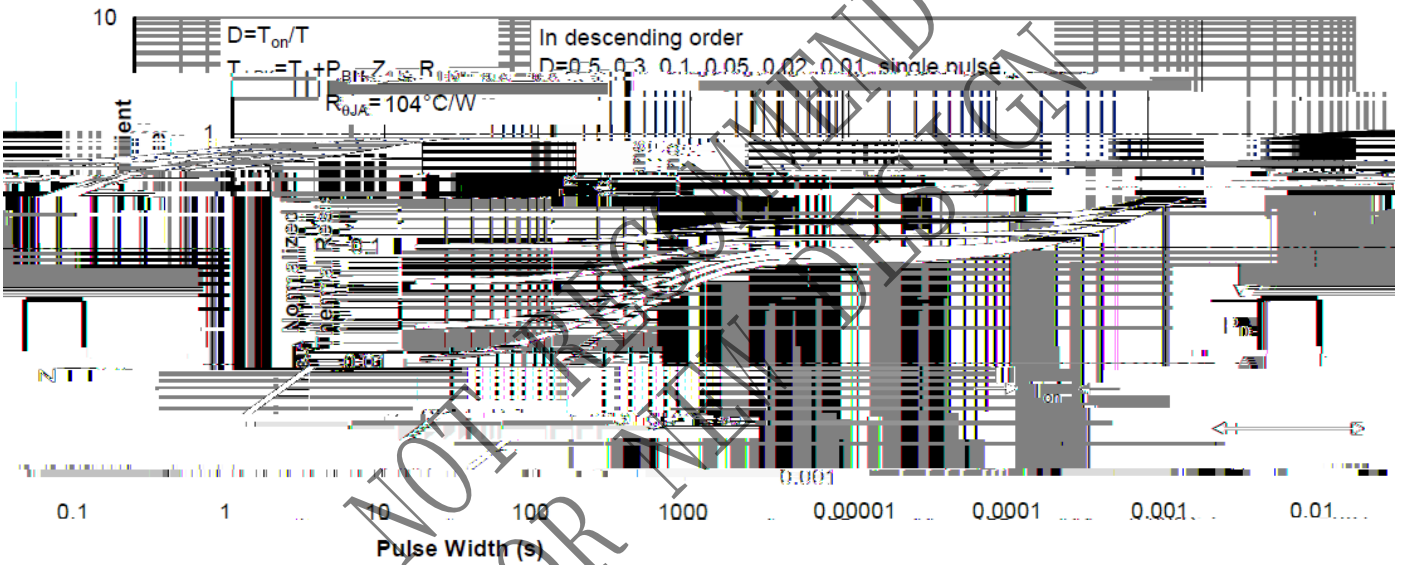


Figure9. Normalized Maximum Transient Thermal Impedance

YJJ3400A

RECOMMEND
YJJ3400B
FOR NEW DESIGN



SOT-23-6L Package information

TOP VIEW

SIDE VIEW

SIDE VIEW

DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.012	0.020	0.300	0.500
B	0.059	0.067	1.500	1.700
C	0.104	0.116	2.650	2.950
D				
G				
H	0.111	0.119	2.820	
J				
K	0.041	0.045	1.050	1.150
L	0.012	0.024	0.300	0.600
M	0.004	0.008	0.100	0.200
θ	0°	8°	0°	8°

NOT RECOMMEND
FOR NEW DESIGN



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie2 8DI1(h)-3(o)9(c)tr3(t)54(o)-3(n)-4(i)c4(s)7()-T3(t)11(e)